

TO-92 Plastic-Encapsulate Transistors

SS8550D331

PNP Transistors

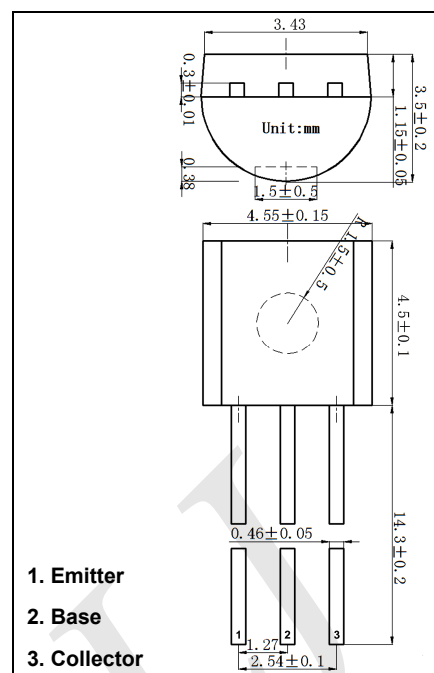
Features

■ Power Dissipation

$P_{CM} : 1W (T_A=25^{\circ}C)$

Maximum Ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-40	V
V_{CEO}	Collector Emitter Voltage	-25	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-1.5	A
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55 ~ 150	$^{\circ}C$



Electrical Characteristics ($T_a=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-40			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1mA, I_B = 0$	-25			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -40V, I_E = 0$			-100	nA
I_{CEO}	Collector cut-off current	$V_{CE} = -20V, I_B = 0$			-100	nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V, I_C = 0$			-100	nA
$h_{FE(1)}$	DC current gain	$V_{CE} = -1V, I_C = -100mA$	160		300	
$h_{FE(2)}$		$V_{CE} = -1V, I_C = -800mA$	40			
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -800mA, I_B = -80mA$			-0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -800mA, I_B = -80mA$			-1.2	V
$V_{BE(on)}$	Base-emitter voltage	$V_{CE} = -1V, I_C = -10mA$			-1	V
C_{ob}	Out capacitance	$V_{CB} = -10V, I_E=0mA, f=1MHZ$			20	pF
f_T	Transition frequency	$V_{CE} = -10V, I_C = -50mA, f=30MHZ$	100			MHz

Typical Characteristics

